# FPF2498

# Adjustable OVP with 28 V Input OVT Load Switch

#### Description

The FPF2498 advanced load-management switch targets applications requiring a highly integrated solution. It disconnects loads powered from the DC power rail (< 12 V) with stringent off-state current targets and high load capacitances (< 100 mF). The FPF2498 consists of a slew-rate controlled low-impedance MOSFET switch. FPF2498 has over-voltage protection and over-temperature protection.

#### Applications

- Cellular Phones, Smart Phones
- Tablets

#### **Related Resources**

• FPF2498 Evaluation Board

#### Features

Function	Advanced Load Switch
Input	3.5 – 12 V
Features	28 V Absolute Ratings on VIN 1.7 A Maximum Continuous Current Capability 80 mΩ RoN Typical Over–Voltage Protection (OVP) Over–Current Protection (OCP) Thermal Shutdown Under–Voltage Lockout (UVLO) Reverse Current Blocking (RCB)
ESD	15 kV IEC 61000–4–2 Air Gap
Operating Temperature Range	−40 to +85 °C
Package	6–Ball WLCSP (1.30 x 1.05 x 0.586 mm, 0.4 mm Pitch)
Ordering Information	FPF2498BUCX
Top Mark	тк



# **ON Semiconductor®**

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WLCSP6 1.30x1.05x0.586 CASE 567RT

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# FPF2498

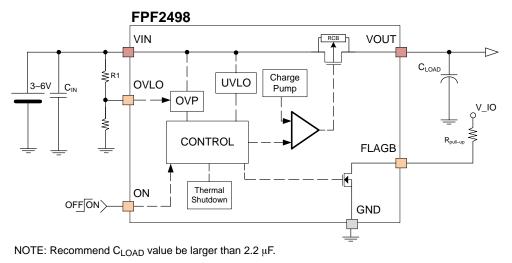
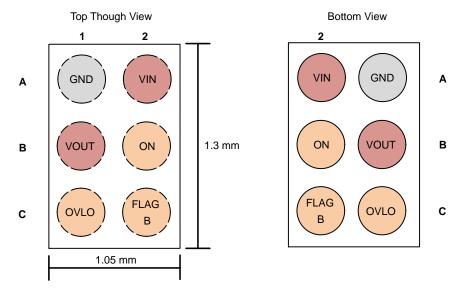


Figure 1. Block Diagram and Typical Application





## Table 1. PIN MAP

Name	Pin #	Туре	Default State	Description				
VIN	A2	Input	N/A	Input voltage path				
VOUT	B1	Output	N/A	Output voltage path				
ON	B2	Input	LOW	On / Off control of device	control of device VIH=HIGH En			
					V <sub>IL</sub> =LOW	Disabled		
OVLO	C1	Input		OVP Adjustment set by R1 and R2 and is compared to 1.2 V				
FLAGB	C2	Open– Drain Output	High–Z	Indicates a OVP / OCP / OTP fault	It LOW / GND Active – Indicates: OVP (over 6.5 V at 3 – 6 OCP (over 2 A) OTP (over 150°C)			
					HIGH / V_IO	Normal Operation		
GND	A1	GND	GND	Device ground				

# PIN CONFIGURATION

#### **Table 2. ABSOLUTE MAXIMUM RATINGS**

Symbol		Min.	Max.	Unit			
V <sub>PIN</sub>	Voltage on VIN to GND, VIN to VOUT	r, ovlo Pins	-0.3	28.0			
	Voltage on ON, FLAGB Pins		-0.3	6.0	V		
	Voltage on VOUT to GND Pins		-0.3	-0.3 20.0			
I <sub>SW</sub>	Maximum Switch Current	Maximum Switch Current		1.75	А		
t <sub>PD</sub>	Total Power Dissipation at $T_A = 25^{\circ}C$			1	W		
TJ	Operating Junction Temperature		-40	+150	°C		
T <sub>STG</sub>	Storage Junction Temperature		-65	+150	°C		
				95 <sup>(1)</sup>	°C/W		
Θја	Thermal Resistance, Junction-to-Am	bient (1-inch Square Pad of 2 oz. Copper)		110 (2)			
ESD	Electrostatic Discharge Capability	Human Body Model, ANSI / ESDA / JEDEC JS-001-2012	3		kV		
		Charged Device Model, JESD22-C101	2				
	IEC61000-4-2 System Level	Air Discharge (V <sub>IN</sub> , V <sub>ON</sub> , V <sub>OUT</sub> to GND)	15				
		Contact Discharge (VIN, VON, VOUT to GND)	8				

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality Measured using 2S2P JEDEC std. PCB.
Measured using 2S2P JEDEC PCB cold plate method.

### Table 3. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameters	Min.	Max.	Unit
V <sub>IN</sub>	Supply Voltage	3.5	12.0	V
I <sub>SW</sub>	Maximum Continues Switch Current (Note 3)		1.7	А
T <sub>A</sub>	Ambient Operating Temperature	-40	85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. Maximum Junction Temperature = 85°C

## **Table 4. ELECTRICAL CHARACTERISTICS**

Unless otherwise noted; V<sub>IN</sub>=3.5 to 5.5 V,  $T_A = -40$  to +85°C; typical values are at V<sub>IN</sub> = 5 V and  $T_A = 25$ °C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Basic Operat	ion					
I <sub>SD(OFF)</sub>	Shutdown Current	$V_{IN}$ = 5.5 V, $V_{OUT}$ = 0 V, $V_{ON}$ = GND		0.4	3.0	μA
Ι <sub>Q</sub>	Quiescent Current	$V_{IN}$ = 5.5 V, $V_{OUT}$ = Floating, $I_{OUT}$ = 0 mA		90	125	μA
R <sub>ON</sub>	On Resistance	V <sub>IN</sub> = 3.7 V, I <sub>OUT</sub> = 200 mA		90		mΩ
		V <sub>IN</sub> = 5.0 V, I <sub>OUT</sub> = 200 mA		80	95 <sup>(5)</sup>	
		V <sub>IN</sub> = 9 V, I <sub>OUT</sub> = 200 mA				
		V <sub>IN</sub> = 12 V, I <sub>OUT</sub> = 200 mA				
V <sub>IH</sub>	ON Input Logic HIGH Voltage	$V_{IN} = 3.5 V$ to 5.5 V	1.15			V
V <sub>IL</sub>	ON Input Logic LOW Voltage	$V_{IN} = 3.5 V$ to 5.5 V			0.65	V
V <sub>OL_FLAG</sub>	FLAGB Output Logic LOW Voltage	V <sub>IN</sub> = 5 V, I <sub>SINK</sub> = 1 mA		0.10	0.20	V
I <sub>FLAGB_LK</sub>	FLAGB Output HIGH Leakage Current	V <sub>IN</sub> = 5 V, Switch On			0.5	μΑ
RPD	Pull-Down Resistance on ON Pin	V <sub>IN</sub> = 5 V, OVLO = GND		3		MΩ

# **FPF2498**

#### **Table 4. ELECTRICAL CHARACTERISTICS**

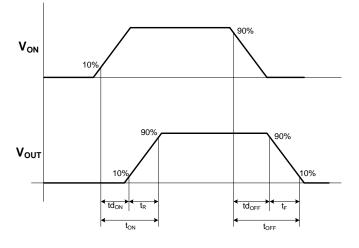
Unless otherwise noted; V<sub>IN</sub>=3.5 to 5.5 V,  $T_A = -40$  to +85°C; typical values are at V<sub>IN</sub> = 5 V and  $T_A = 25$ °C.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Over-Voltage	Protection					
V <sub>OV_TRIP</sub>	Default Input OVP Lockout	$V_{IN}$ Rising Threshold OVLO = GND	6.2	6.5	6.8	
		$V_{IN}$ Falling Threshold OVLO = GND		6.2		V
V <sub>OVLO_SEL</sub>	Voltage threshold for OVLO selection	$V_{IN}$ = 3.5 V to 5.5 V, OVLO = GND		0.3		V
V <sub>OVP_HYS</sub>	Input OVP Hysteresis	V <sub>IN</sub> Falling Threshold OVLO = External Setting		0.3		V
V <sub>OVLO_TH</sub>	OVLO Set Threshold	$V_{IN} = 3.5$ to $V_{OVLO}$		1.20		V
t <sub>OVP</sub>	Response Time	$I_{OUT} = 0.5 \text{ A}, C_L = 0 \ \mu\text{F}, T_A = 25^{\circ}\text{C}, V_{IN} = 6 \ V \ \text{to} \ 7 \ V$		0.5	1	μs
V <sub>UVLO</sub>	Under-Voltage Lockout	V <sub>IN</sub> Rising		3.2		
		V <sub>IN</sub> Falling		3.0		V
V <sub>UVLO_HYS</sub>	UVLO Hysteresis			200		mV
I <sub>RCB</sub>	RCB Current	V <sub>ON</sub> = 0 V, V <sub>OUT</sub> = 5.5 V, V <sub>IN</sub> = 0 V		2	5	μA
TSD	Thermal Shutdown	Shutdown Threshold		150		°C
		Return from Shutdown		130		
		Hysteresis		20		
Over-Curren	t Protection					
I <sub>OCP</sub>	Over-Current Protection Trip Point	I <sub>SW</sub> > I <sub>OCP</sub>		2		А
Dynamic Cha	racteristics					
t <sub>DON</sub>	Turn–On Delay <sup>(6)</sup>	$V_{IN} = 5 V$ , $R_L = 100 Ω$ , $C_L = 10 μF$ , $T_A = 25°C$		4.3		ms
t <sub>R</sub>	V <sub>OUT</sub> Rise Time <sup>(6)</sup>	TA - 23 C		3.0		ms
t <sub>ON</sub>	Turn–On Time <sup>(7)</sup>			7.3		ms
t <sub>DOFF</sub>	Turn–Off Delay <sup>(5, 6)</sup>			600		μs
t <sub>F</sub>	V <sub>OUT</sub> Fall Time <sup>(5, 6)</sup>			2.0		ms
tOFF	Turn–Off Time <sup>(7, 8)</sup>			2.5		ms
t <sub>READY</sub>	Time for Device Ready for Large Load Current <sup>(9)</sup>	C <sub>L</sub> = 10 μF		5		ms
t <sub>RESTART</sub>	Over-Current Blanking Time (5)	$V_{IN} = 5 \text{ V } I_{OUT} \ge 1.7 \text{ A}$		64		ms
t <sub>OCP</sub>	Over-Current Response Time <sup>(5)</sup>	Moderate Over–Current Condition; $IOUT \ge ILIM VOUT \le VIN$		4		μs
<sup>t</sup> HOCP	Hard Over-Current Response Time	Moderate Over–Current Condition; IOUT $\ge$ ILIM VOUT $\le$ 0 V		3		μs
FLAGB_Release	Over-Current/Voltage/Temp. Flag Release Time <sup>(5)</sup>	e Time for Flag to Release when Fault Condition Removed		100		ms

4.  $T_A = 25^{\circ}C$ 5. This parameter is guaranteed by design and characterization; not production tested. 6.  $t_{DON}/t_{DOFF}/t_R/t_F$  are defined in figure below. 7.  $t_{ON} = t_R + t_{DON}$ . 8. tOFF = tF + tDOFF. 9. After the transmission of tra

9. After t<sub>READY</sub>, the device is ready for maximum DC current load condition.

# TIMING DIAGRAM



 $\label{eq:t_DON} \begin{array}{l} \text{t}_{DON} = \text{Delay On Time}; \\ t_R = V_{OUT} \mbox{ Rise Time}; \\ t_{ON} = Turn-On \mbox{ Time}; \\ t_{DOFF} = Delay \mbox{ Off Time}; \\ t_F = V_{OUT} \mbox{ Fall Time}; \\ t_{OFF} = Turn \mbox{ Off Time} \end{array}$ 

where:

Figure 3. Timing Diagram



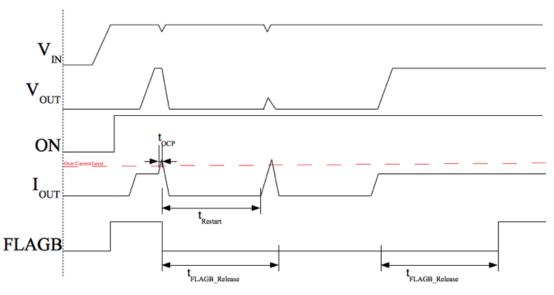


Figure 4. OCP Turn–Off Timing Diagram

#### **OPERATION AND APPLICATION DESCRIPTION**

#### Input Capacitor

To limit the voltage drop on the input supply caused by transient inrush current when the switch turns on into discharge load capacitor; a capacitor must be placed between the VIN and GND pins. A high–value  $C_{IN}$  capacitor can be used to reduce the voltage drop in high–current applications.

### **Output Capacitor**

An output capacitor should be placed between the VOUT and GND pins. This capacitor prevents parasitic board inductance from forcing  $V_{OUT}$  below ground when the switch is on. This capacitor also prevents reverse inrush current from creating a voltage spike that could damage the device in the case of a  $V_{OUT}$  short.

### Fault Reporting

Upon the detection of an over-voltage, over-current, or over-temperature condition, the FLAGB signals the fault by activating LOW.

### Under-Voltage Lockout (UVLO)

The under–voltage lockout turns the switch off if the input voltage drops below the lockout threshold. With the ON pin active, the input voltage rising above the UVLO threshold releases the lockout and enables the switch.

### Over-Voltage Lockout (OVLO)

The OVLO pin sets the over–voltage lockout trip point with a resistor–divider network. OVLO adjustment is set by R1 and R2 and is compared to 1.2 V. When  $V_{IN} \times R2$  / (R1+R2) >1.2 V, which means  $V_{IN} > V_{OVLO}$ , the switch turns off to ensure protection to devices connected to

VOUT. A 1 M $\Omega$  or larger resistor is recommended on R1 to reduce standby power consumption. To use the default values of 5.8 V for V<sub>OVLO</sub> connect the OVLO pin directly to GND.

## Reverse-Current Blocking (RCB)

The reverse–current blocking feature protects the input source against current flow from output to input. When the load switch is OFF, no current flows from the output to input.

### Thermal Shutdown (TSD)

Thermal shutdown protects the die from internally or externally generated excessive temperature. During an over-temperature condition, the switch is turned off. The switch automatically turns on again if the temperature of the die drops below the threshold temperature.

### **Current Limit**

The current limit ensures that the current flow though the switch doesn't exceed a maximum value, which can damage the device. If the current flow though the switch exceeds the trip point, the switch turns off and enters the blanking time. After the blanking time, the switch is re–enabled and checks if the fault still exists.

### **Board Layout**

For best performance, all traces should be as short as possible. The input and output capacitors should be placed close to the device to minimize the effect that parasitic trace inductance may have on normal and short–circuit operation. Using wide traces for VIN, VOUT, GND minimizes parasitic electrical effects along with minimizing the case–to–ambient thermal impedance.

#### Table 5. PACKAGE SPECIFIC DIMENSIONS

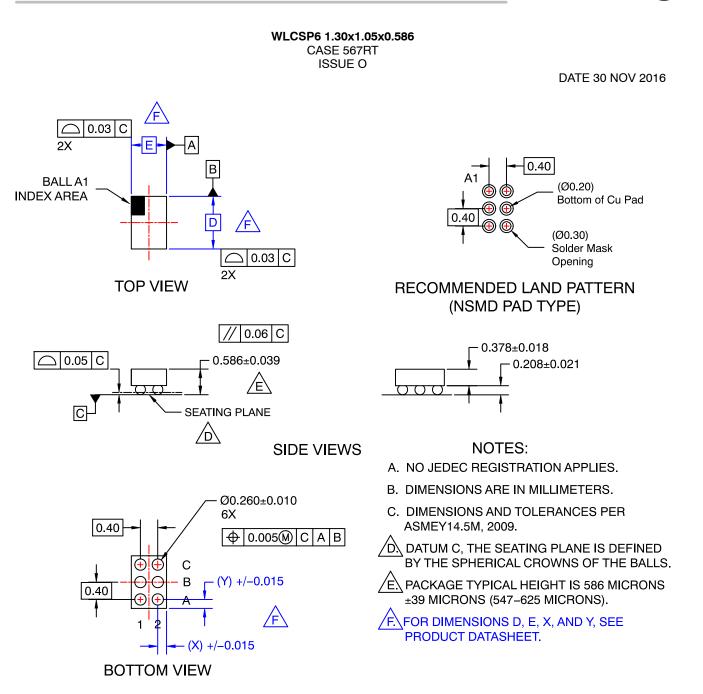
D	E	X	Y
$1.300\pm0.030$	$1.050\pm0.030$	0.325	0.250

#### **ORDERING INFORMATION**

Part Number	Operating Temperature	Package	Packing Method <sup>†</sup>
FPF2498BUCX	–40°C to 85°C	WLCSP6 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D





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